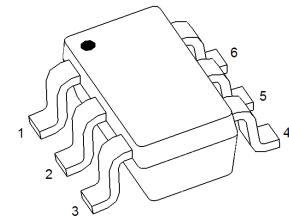


## 8205A Dual N-Channel MOSFET

<b>V<sub>(BR)DSS</sub></b>	<b>R<sub>D(on)MAX</sub></b>	<b>I<sub>D Max</sub></b>
20V	0.022Ω @ 4.5V	5.0A
	0.030Ω @ 2.5V	

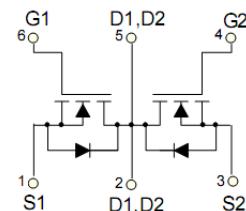
SOT-23-6



Equivalent Circuit

### FEATURE

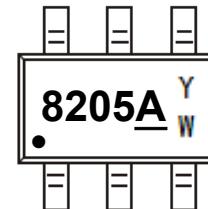
- TrenchFET Power MOSFET
- Excellent R<sub>D(on)</sub>
- Low Gate Charge
- High Power and Current Handling Capability
- Surface Mount Package



MARKING

### APPLICATION

- Battery Protection
- Load Switch
- Power Management



Y :year code W :week code

### ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current	I <sub>D</sub>	5	A
Pulsed Drain Current (note 1)	I <sub>DM</sub>	15	A
Thermal Resistance from Junction to Ambient (note 2)	R <sub>θJA</sub>	100	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~+150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T <sub>L</sub>	260	°C

T<sub>a</sub>=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>STATIC CHARACTERISTICS</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA	20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 18V, V <sub>GS</sub> = 0V			500	nA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage (note 3)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA	0.5	0.7	1.0	V
Drain-source on-resistance (note 3)	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A		19	22	mΩ
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4A		24	30	mΩ
Forward transconductance (note 3)	g <sub>F</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 5A		10		S
Diode forward voltage (note 3)	V <sub>SD</sub>	I <sub>S</sub> = 1.25A, V <sub>GS</sub> = 0V			1.2	V
<b>DYNAMIC CHARACTERISTICS (note 4)</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz		800		pF
Output Capacitance	C <sub>oss</sub>			155		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			125		pF
<b>SWITCHING CHARACTERISTICS (note 4)</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4V, I <sub>D</sub> = 1A, R <sub>GEN</sub> = 10Ω		18		ns
Turn-on rise time	t <sub>r</sub>			4.8		ns
Turn-off delay time	t <sub>d(off)</sub>			43.5		ns
Turn-off fall time	t <sub>f</sub>			20		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4A		11		nC
Gate-Source Charge	Q <sub>gs</sub>			2.2		nC
Gate-Drain Charge	Q <sub>gd</sub>			2.5		nC

#### Notes :

1. Repetitive rating: Pulse width limited by maximum junction temperature
2. Surface Mounted on FR4 board, t ≤ 10 sec.
3. Pulse test : Pulse width ≤ 300µs, duty cycle ≤ 2%.
4. Guaranteed by design, not subject to production.

## Typical Electrical and Thermal Characteristics

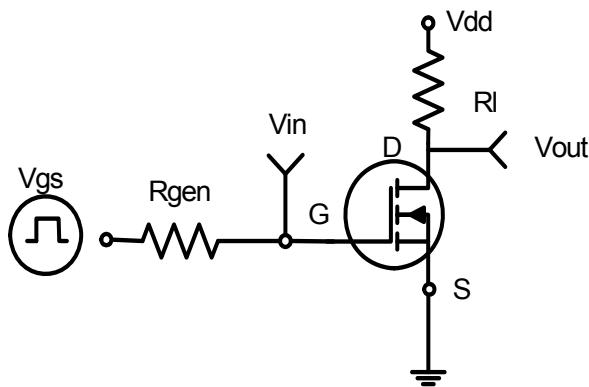


Figure 1:Switching Test Circuit

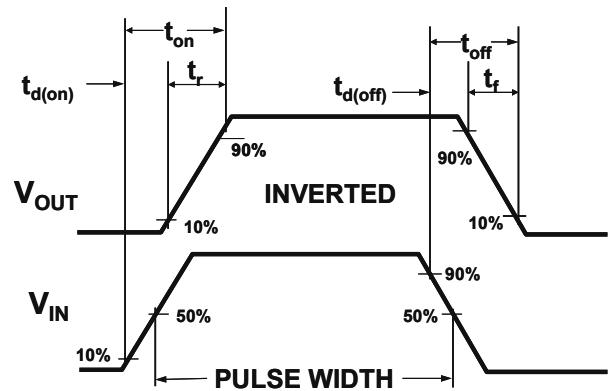


Figure 2:Switching Waveforms

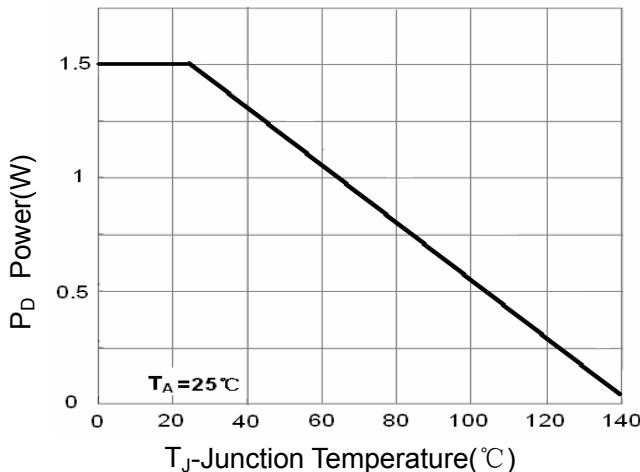


Figure 3 Power Dissipation

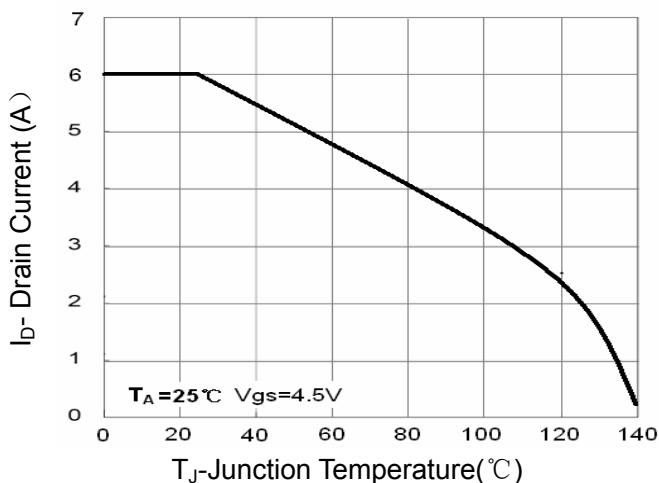


Figure 4 Drain Current

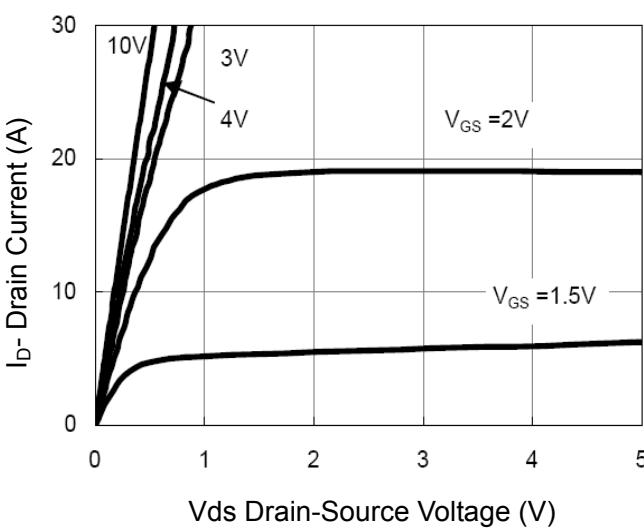


Figure 5 Output Characteristics

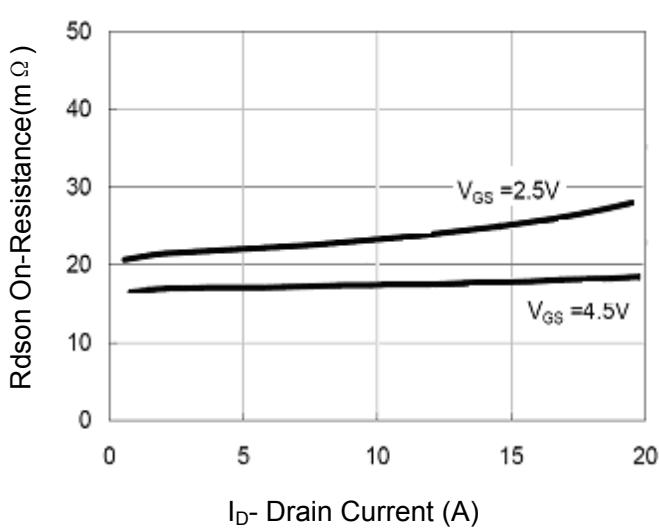
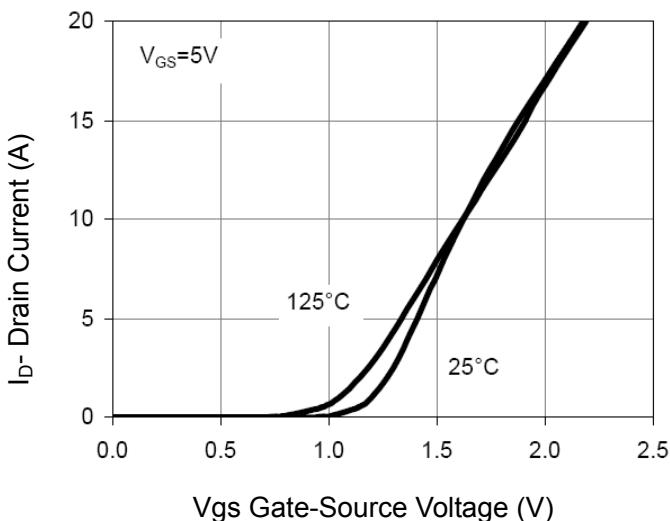
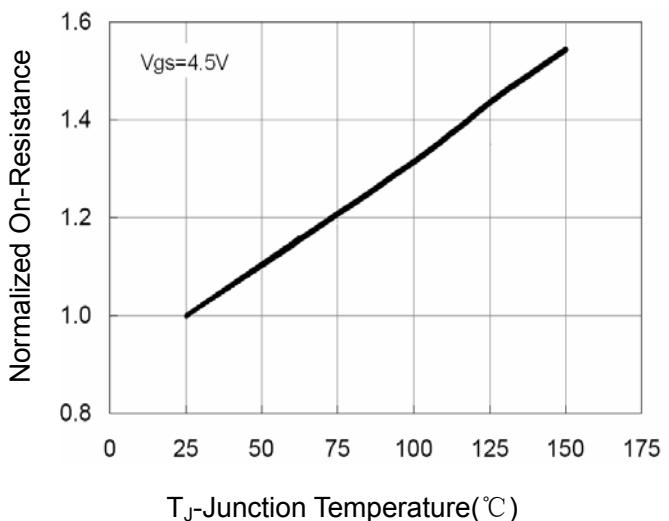


Figure 6 Drain-Source On-Resistance

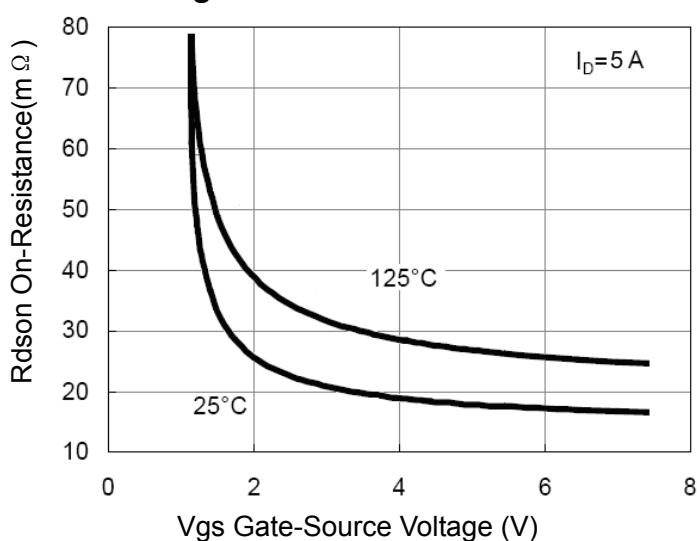
# 8205A



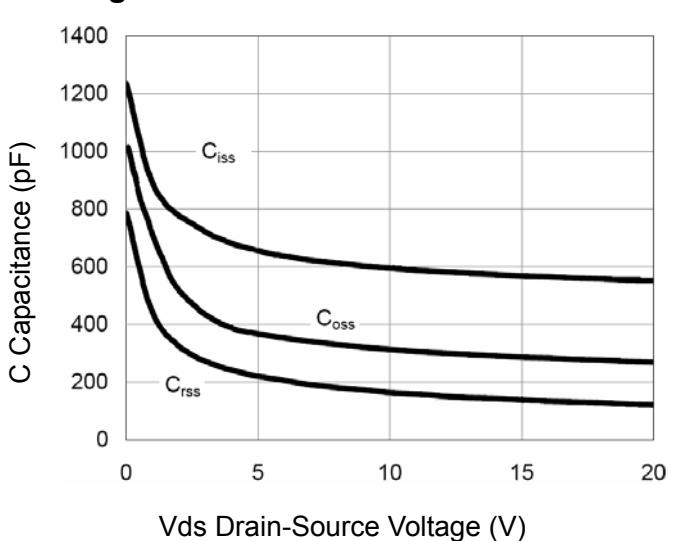
**Figure 7 Transfer Characteristics**



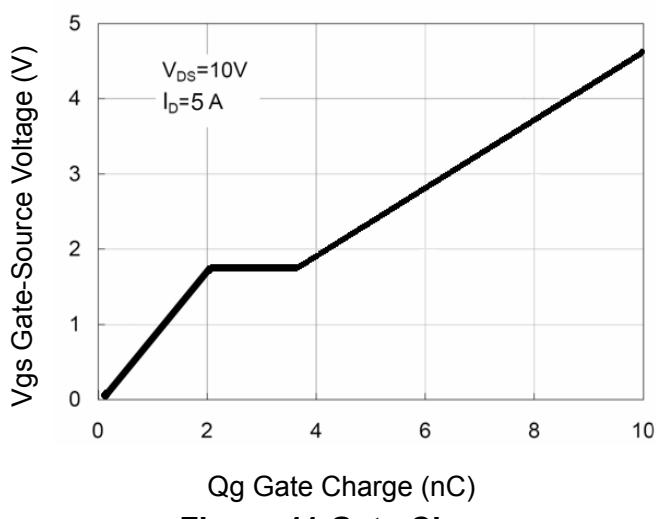
**Figure 8 Drain-Source On-Resistance**



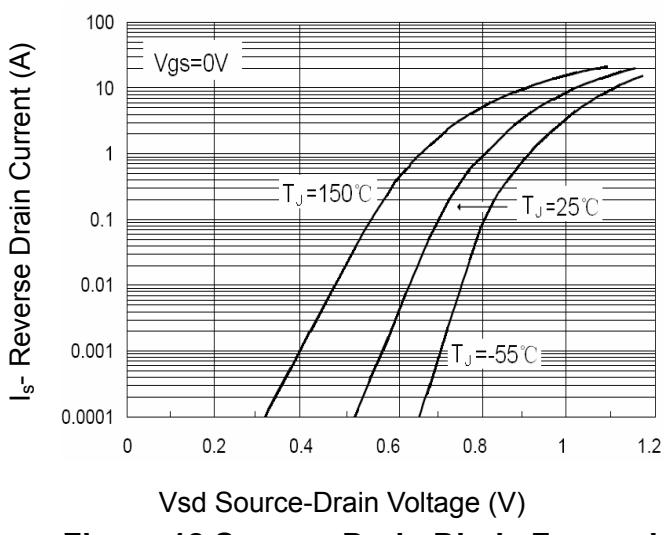
**Figure 9  $R_{DS(on)}$  vs  $V_{GS}$**



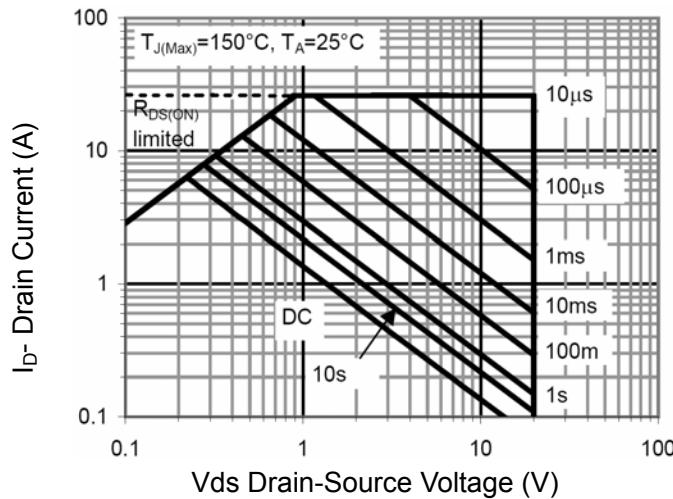
**Figure 10 Capacitance vs  $V_{DS}$**



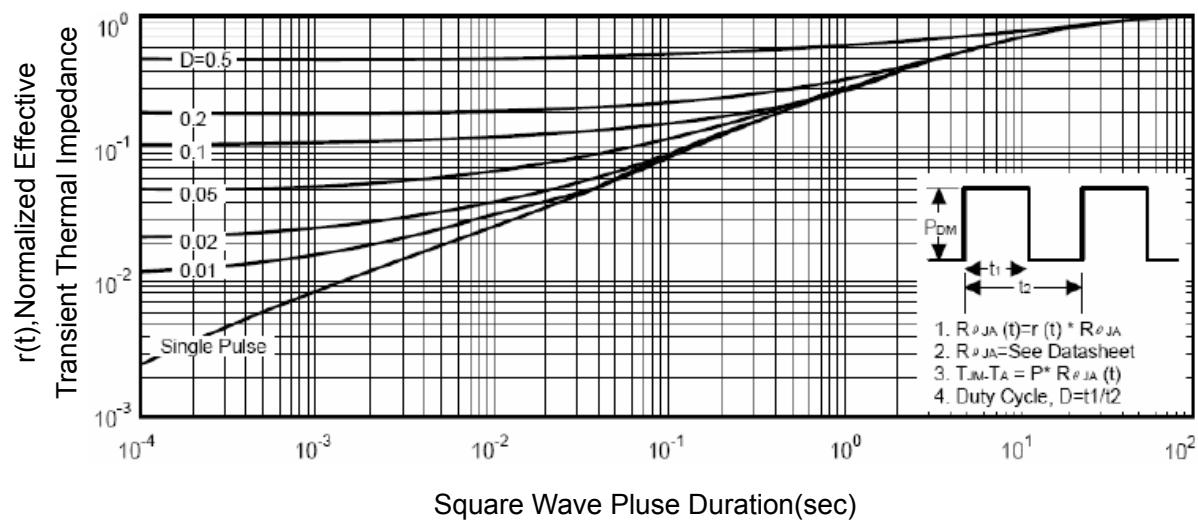
**Figure 11 Gate Charge**



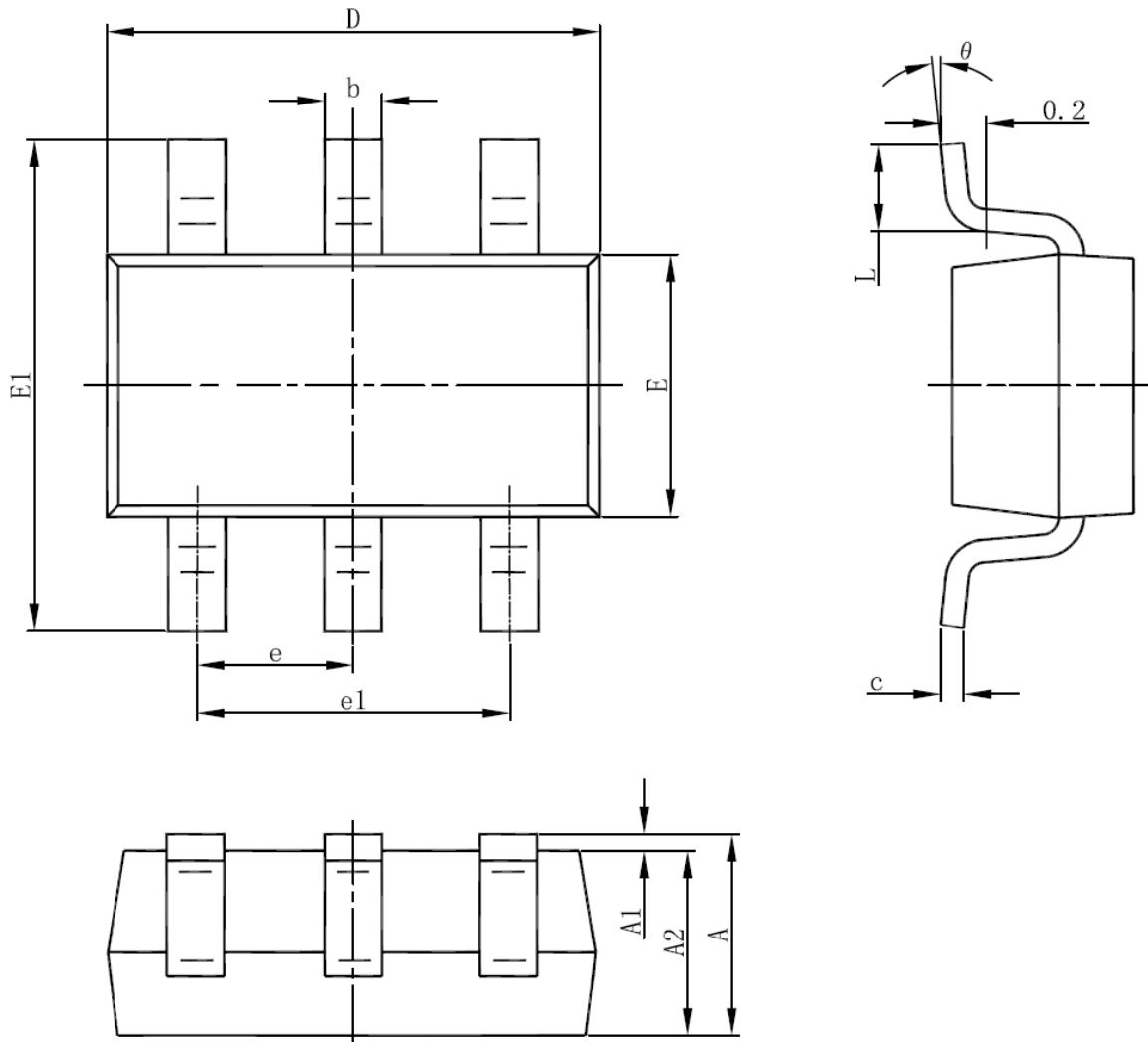
**Figure 12 Source- Drain Diode Forward**



**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

**SOT23-6 Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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